

GSDBAV99

Switching Diodes

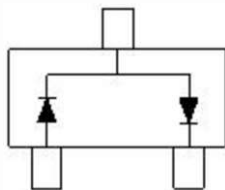
Product Description

Switching Diode 215mA / 75V

Features

- General Purpose Switching Applications
- Low Current Leakage
- Fast Switching Speed
- RoHS Compliant

Equivalent Circuit Diagram



SOT-23

Ordering and Marking Information

Part Number	Package	Quantity	Part Marking
GSDBAV99F	SOT- 23	3,000 PCS	A7

Absolute Maximum Ratings

(T_A=25°C Unless Otherwise specified)

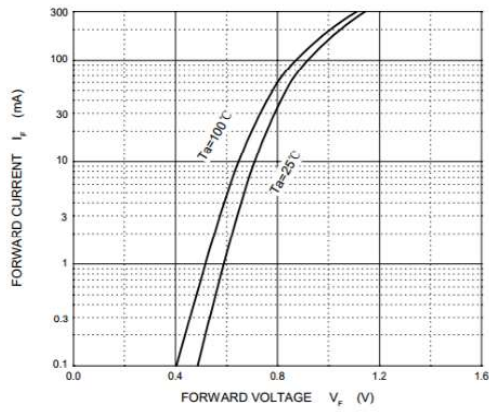
Symbol	Parameter	Value	Units
V _R	Reverse Voltage	75	V
I _F	Forward Current	215	mA
I _{FSM}	Non-Repetitive Peak Forward Surge Current (t = 1.0 μs)	2.0	A
P _D	Power Dissipation	225	mW
R _{θJA}	Thermal Resistance from Junction to Ambient *	556	°C/W
T _J	Max Junction Temperature	+150	°C
T _{STG}	Storage Temperature Range °C	-55 to + 150	°C

Electrical Characteristics

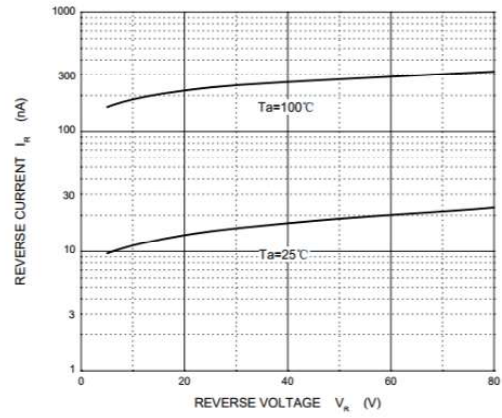
(T_A=25°C Unless Otherwise specified)

Symbol	Parameter	Test Condition	Min	Max	Units
V _R	Breakdown Voltage	I _R =100μA	75	-	V
I _R	Reverse Leakage Current	V _R =70V	-	2.5	μA
V _F	Forward Voltage	I _F = 1mA I _F = 10mA I _F = 50mA I _F = 150mA	-	0.715 0.855 1.000 1.250	V
C _T	Capacitance between leads	V _R =0V, f = 1MHz	-	2.0	pF
t _{rr}	Reverse Recovery Time	I _F =10mA, V _R =6V R _L =100Ω, I _{RR} =1mA	-	6	ns

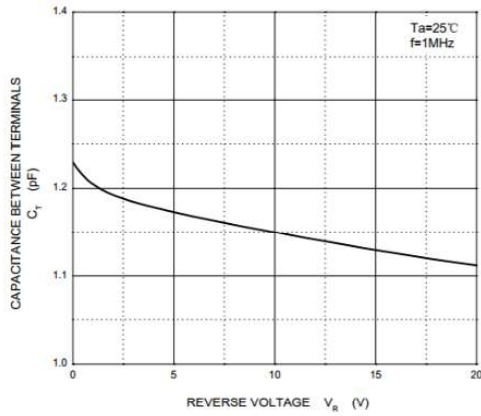
Typical Characteristics



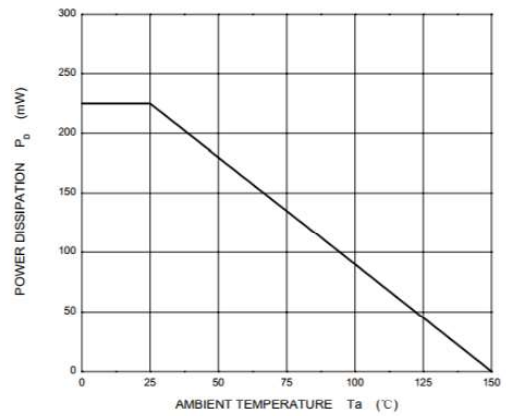
Forward Characteristics



Reverse Characteristics



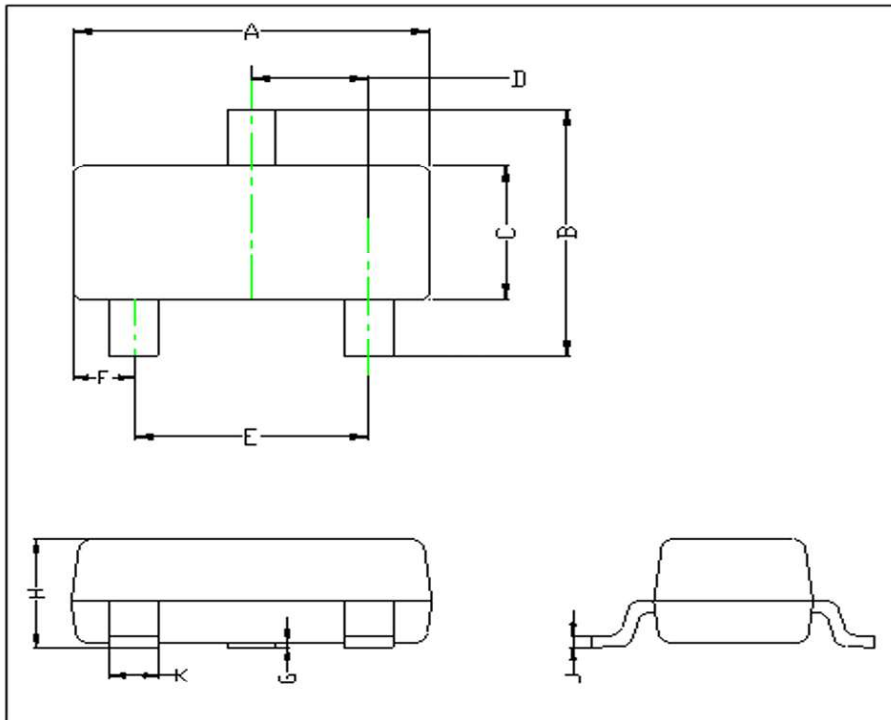
Capacitance Characteristics



Power Derating Curve

Package Dimension

SOT-23







Dimensions



Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	2.80	3.04	0.110	0.120
B	2.10	2.64	0.082	0.104
C	1.20	1.40	0.047	0.055
D	0.89	1.03	0.035	0.041
E	1.78	2.05	0.070	0.081
F	0.45	0.60	0.017	0.024
G	0.01	0.10	0.000	0.004
H	0.90	1.11	0.035	0.044
J	0.09	0.18	0.003	0.007
K	0.37	0.51	0.014	0.020

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